

v00.1115

GaAs MMIC I/Q MIXER 4 - 8.5 GHz

Typical Applications

The HMC525ALC4 is ideal for:

- Point-to-Point and Point-to-Multi-Point Radio
- VSAT

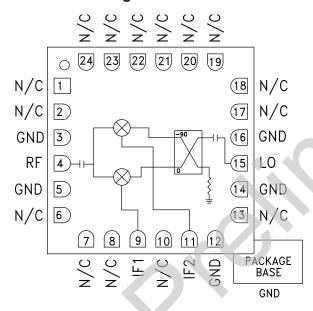
Features

Wide IF Bandwidth: DC - 3.5 GHz

Image Rejection: 40 dB LO to RF Isolation: 50 dB High Input IP3: +23 dBm

24 Lead 4x4mm SMT Package: 16mm²

Functional Diagram



General Description

The HMC525ALC4 is a compact I/Q MMIC mixer in a leadless "Pb free" RoHS compliant SMT package, which can be used as either an Image Reject Mixer or a Single Sideband Upconverter. The mixer utilizes two standard Hittite double balanced mixer cells and a 90 degree hybrid fabricated in a GaAs MESFET process. A low frequency quadrature hybrid was used to produce a 100 MHz USB IF output. This product is a much smaller alternative to hybrid style Image Reject Mixers and Sideband Upconverter assemblies. The HMC525ALC4 eliminates the need for wire allowing bonding use surface mount manufacturing techniques.

Electrical Specifications, $T_{\Delta} = +25$ °C, IF= 100 MHz, LO = +15 dBm*

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range, RF/LO	4.0 - 8.5			5.5 - 7.5			GHz
Frequency Range, IF	DC - 3.5			DC - 3.5			GHz
Conversion Loss (As IRM)		8	11		7.5	9.5	dB
Image Rejection	20	35		30	40		dB
1 dB Compression (Input)		+14			+15		dBm
LO to RF Isolation	33	45		40	50		dB
LO to IF Isolation	14	20		17	20		dB
IP3 (Input)		+23			+23		dBm
Amplitude Balance		0.3			0.2		dB
Phase Balance		8			4		Deg

^{*} Unless otherwise noted, all measurements performed as downconverter.



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Harmonics of LO

LO From (CLIE)	nLO Spur at RF Port					
LO Freq. (GHz)	1	2	3	4		
3.5	40	40	54	50		
4.5	43	45	58	53		
5.5	51	57	48	67		
6.5	59	63	64	56		
7.5	48	66	64	62		
8.5	44	65	60	67		
LO = +15 dBm						

Values in dBc below input LO level measured at RF Port.

Absolute Maximum Ratings

	_
RF / IF Input	+20 dBm
LO Drive	+27 dBm
Channel Temperature	150°C
Continuous Pdiss (T=85°C) (derate 9.7 mW/°C above 85°C)	631 mW
Thermal Resistance (R _{TH}) (junction to die bottom)	103 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C

MxN Spurious Outputs

	nLO						
mRF	0	1	2	3	4		
0	xx	-11	32	23	51		
1	32	0	42	51	66		
2	89	62	74	65	89		
3	89	89	89	82	89		
4	89	89	89	89	89		

RF = 5.6 GHz @ -10 dBm

LO = 5.5 GHz @ +15 dBm

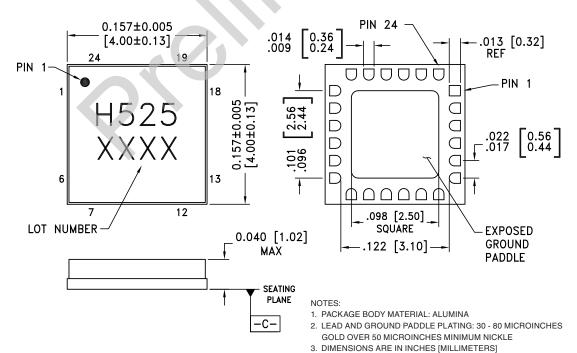
Data taken without IF hybrid

All values in dBc below IF power level



Outline Drawing

BOTTOM VIEW



6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED

4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM

TO PCB RF GROUND